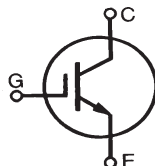


GenX3™ 600V IGBTs

IXGK320N60B3 IXGX320N60B3

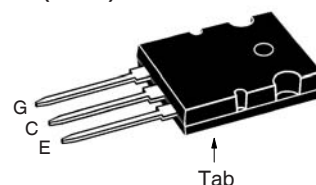
$$\begin{aligned} V_{CES} &= 600V \\ I_{C90} &= 320A \\ V_{CE(sat)} &\leq 1.6V \end{aligned}$$

Medium-Speed Low-Vsat PT
IGBTs for 5-40 kHz Switching

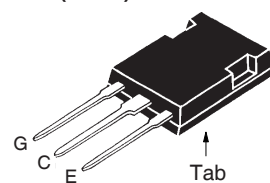


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	500	A
I_{C90}	$T_C = 90^\circ\text{C}$	320	A
I_{LRMS}	Terminal Current Limit	160	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	1200	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 320$ $V_{CE} \leq V_{CES}$	A V
P_C	$T_C = 25^\circ\text{C}$	1700	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ\text{C}$
M_d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXGX)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247 (IXGX)



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for Low Conduction and Switching Losses
- High Current Capability
- Square RBSOA

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1\text{mA}$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 4\text{mA}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			75 μA 2 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 400 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1 $I_C = 320A$		1.4 2.0	1.6 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 1	70	125	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		18	nF
C_{oes}			960	pF
C_{res}			130	pF
Q_g	$I_C = 320\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		585	nC
Q_{ge}			105	nC
Q_{gc}			215	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$		44	ns
t_{ri}			66	ns
E_{on}			2.7	mJ
$t_{d(off)}$			250	ns
t_{fi}			165	ns
E_{off}	$V_{CE} = 0.8 \cdot V_{CES}$, $R_G = 1\Omega$		3.5	5.0 mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$		40	ns
t_{ri}			67	ns
E_{on}			3.5	mJ
$t_{d(off)}$			330	ns
t_{fi}			265	ns
E_{off}	$V_{CE} = 0.8 \cdot V_{CES}$, $R_G = 1\Omega$		5.4	mJ
R_{thJC}			0.15	0.073°C/W
R_{thCS}				$^\circ\text{C/W}$

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

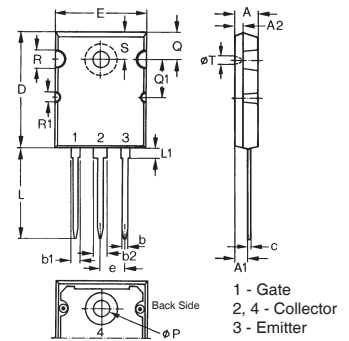
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

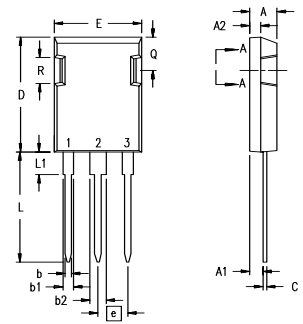
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 AA (IXGK) Outline



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ (IXGX) Outline



Terminals: 1 - Gate
2 - Collector
3 - Emitter

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

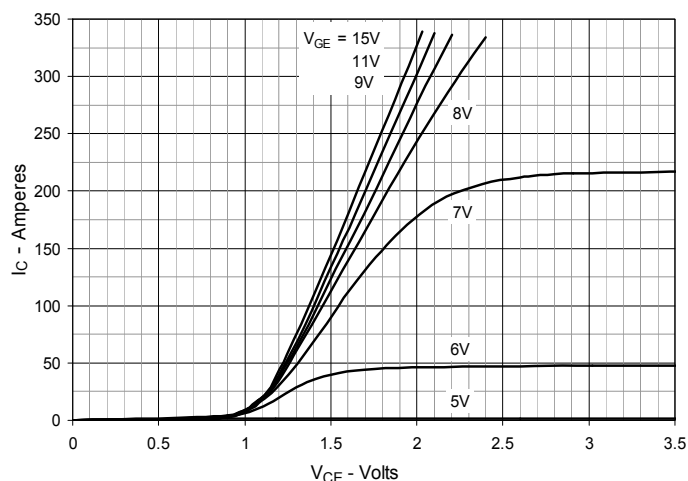


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

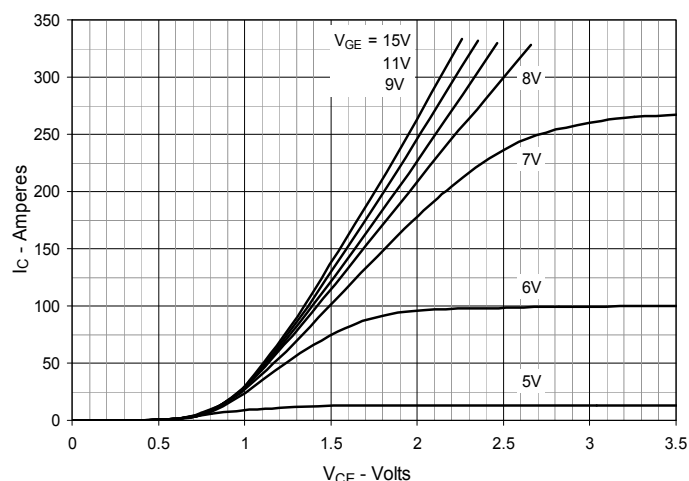


Fig. 3. Dependence of $V_{CE(sat)}$ on Junction Temperature

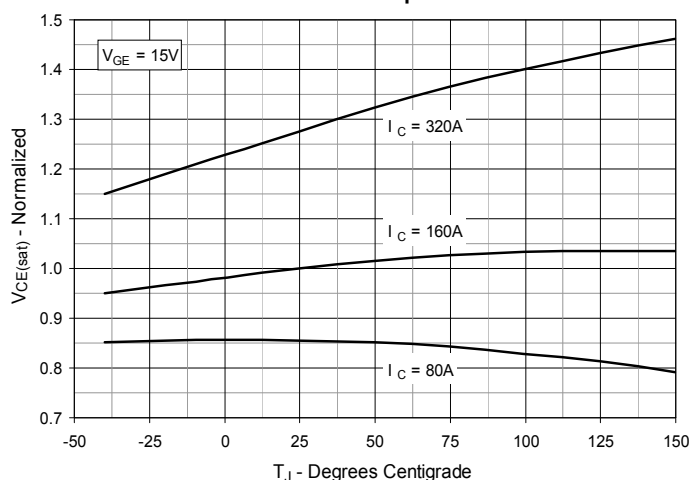


Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

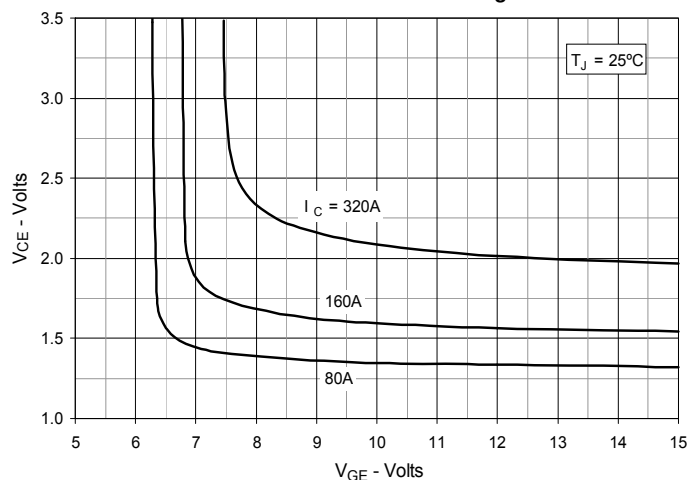


Fig. 5. Input Admittance

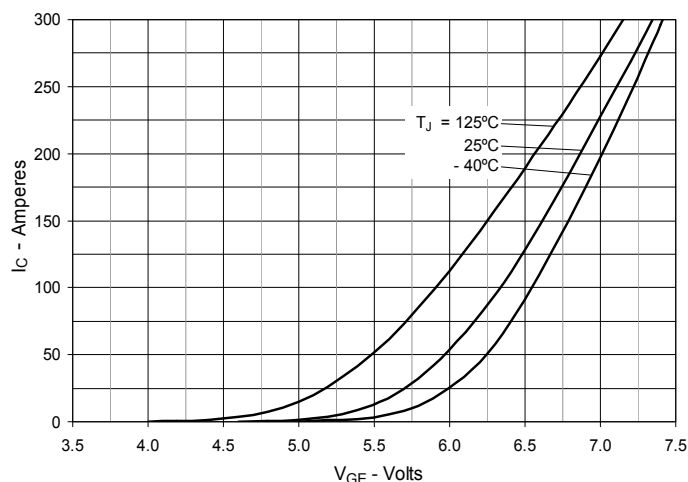


Fig. 6. Transconductance

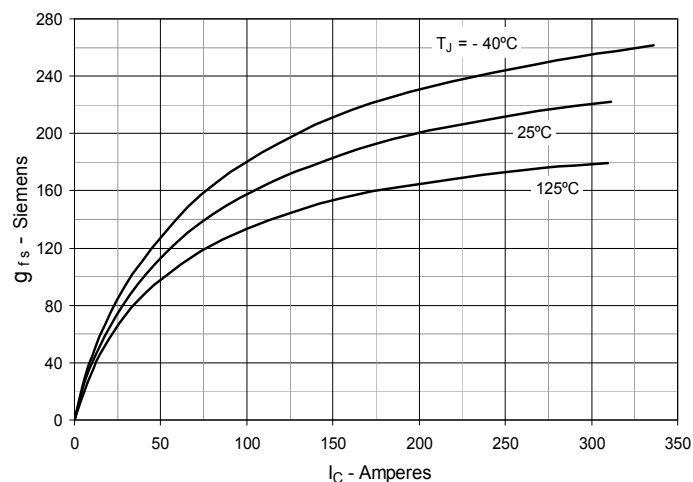


Fig. 7. Gate Charge

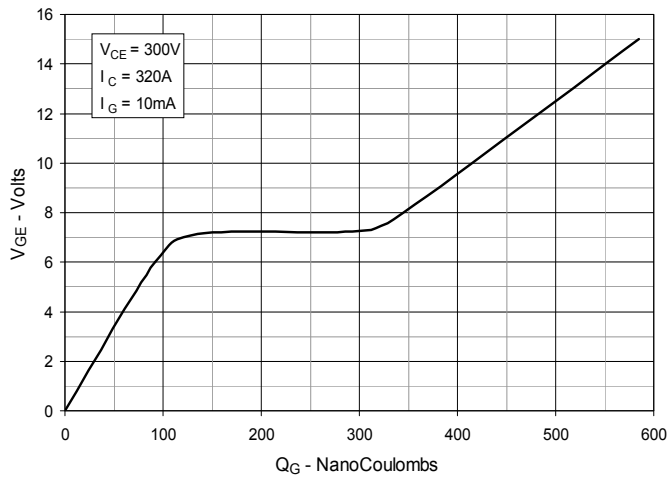


Fig. 8. Capacitance

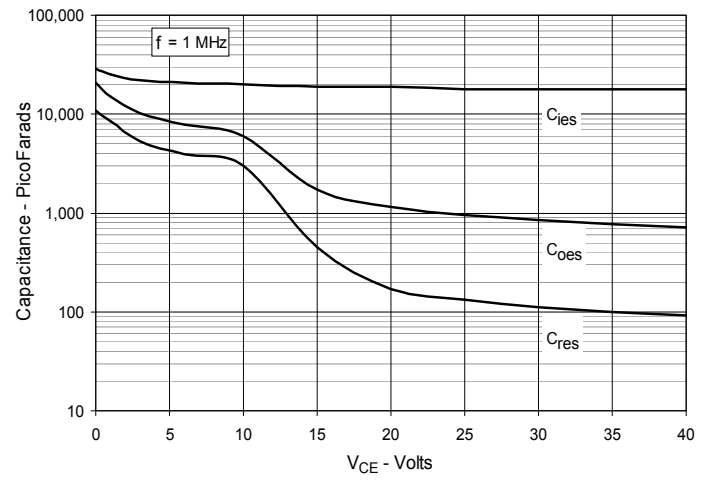


Fig. 9. Reverse-Bias Safe Operating Area

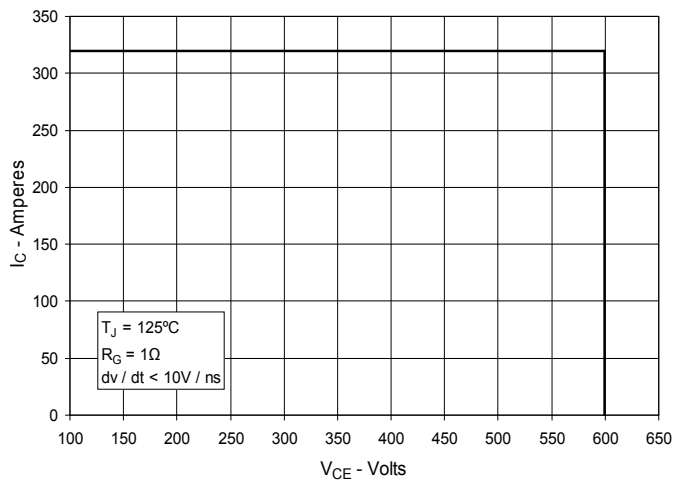


Fig. 10. Maximum Transient Thermal Impedance

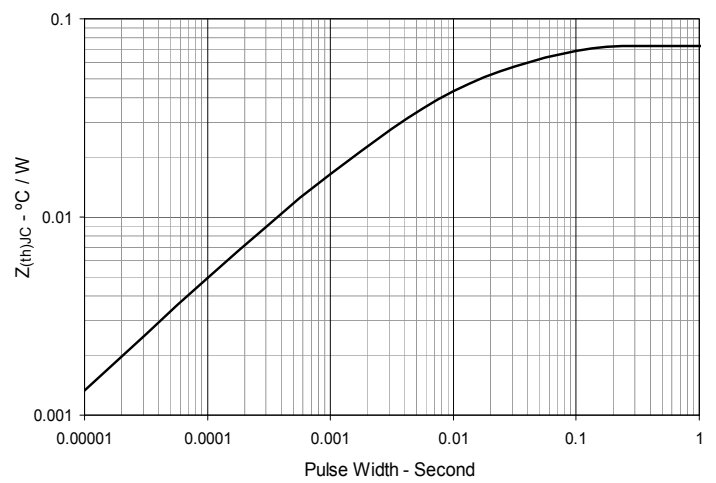


**Fig. 11. Inductive Switching
Energy Loss vs. Gate Resistance**

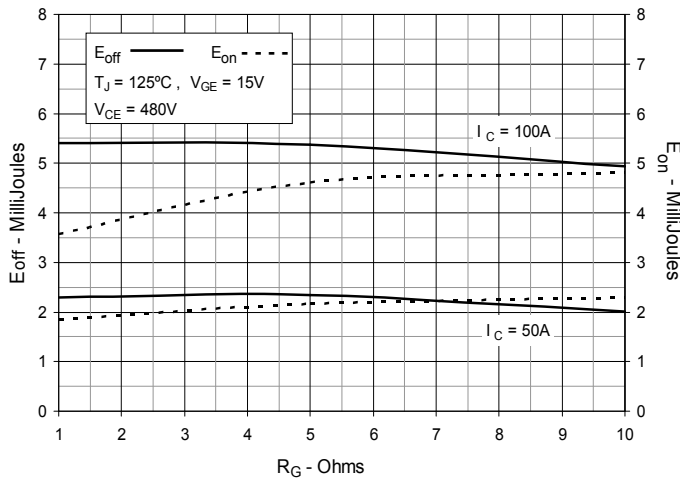


**Fig. 12. Inductive Switching
Energy Loss vs. Collector Current**

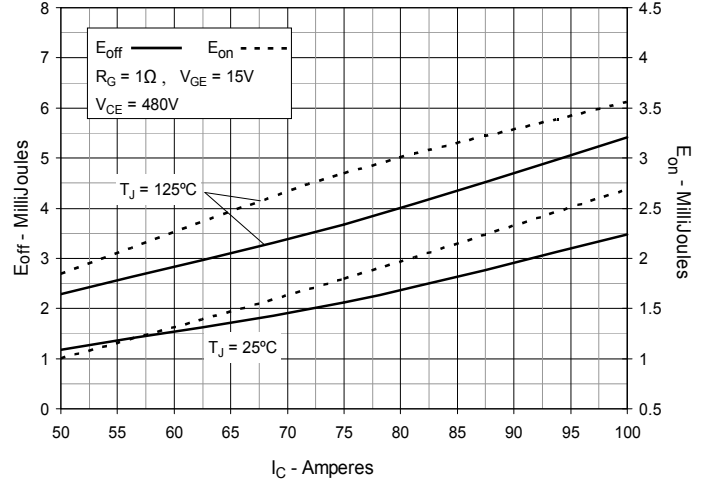


**Fig. 13. Inductive Switching
Energy Loss vs. Junction Temperature**

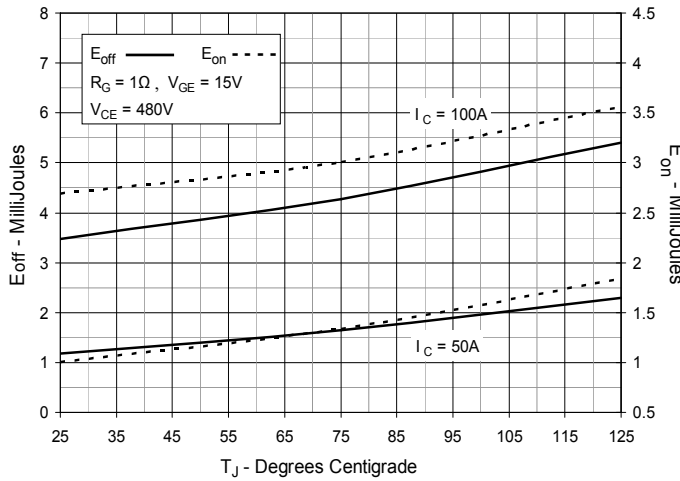


**Fig. 14. Inductive Turn-off
Switching Times vs. Gate Resistance**

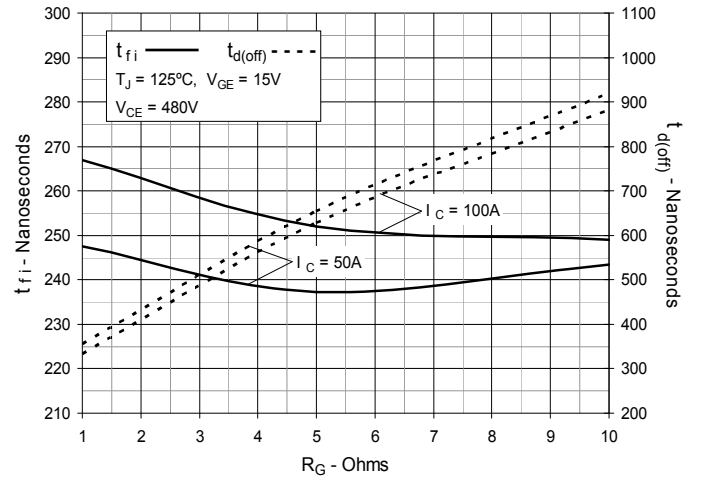


**Fig. 15. Inductive Turn-off
Switching Times vs. Collector Current**

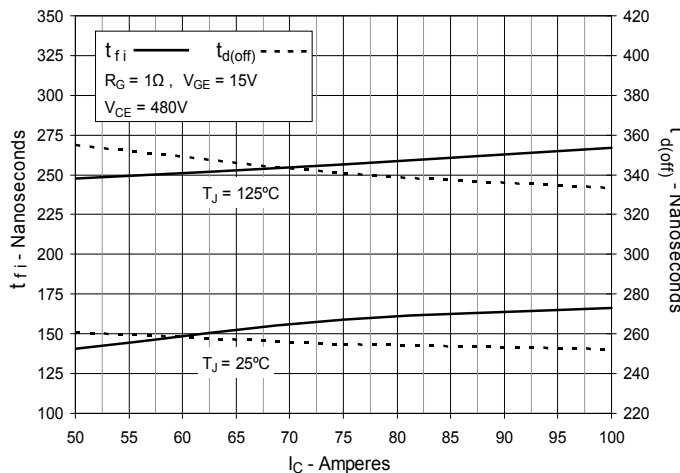


**Fig. 16. Inductive Turn-off
Switching Times vs. Junction Temperature**

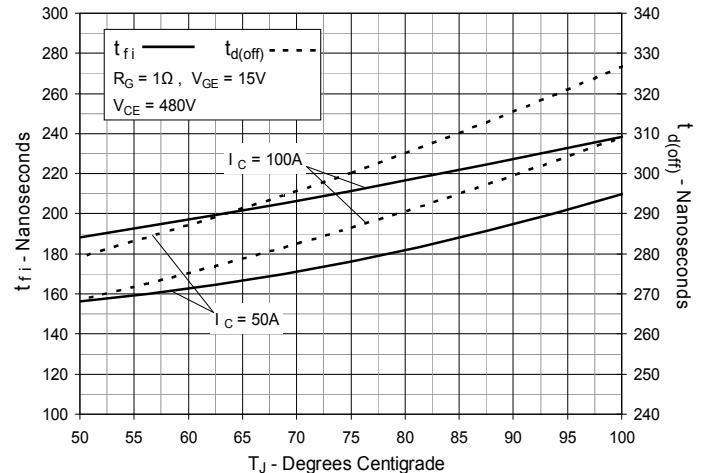


**Fig. 17. Inductive Turn-on
Switching Times vs. Gate Resistance**

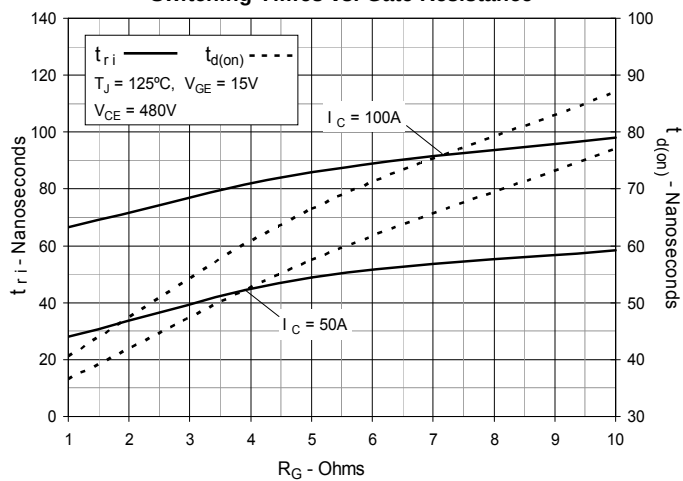


**Fig. 18. Inductive Turn-on
Switching Times vs. Collector Current**

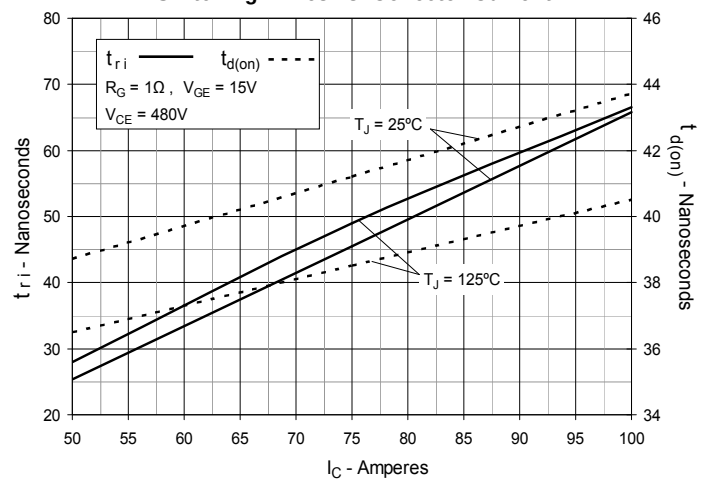


**Fig. 19. Inductive Turn-on
Switching Times vs. Junction Temperature**

